





30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Max R _{DS(ON)}	Max I D @ T _A = +25°C
	1Ω @ V _{GS} = -4.5V	-0.62A
-30V	1.5Ω @ $V_{GS} = -2.5V$	-0.5A
	2Ω @ V _{GS} = -1.8V	-0.44A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load switches in portable electronics

Features and Benefits

- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

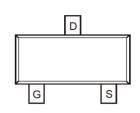




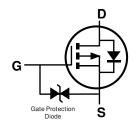


SOT23

Top View



Top View Internal Schematic



Equivalent Circuit

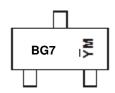
Ordering Information (Note 4)

Part Number	Package	Packing		
	rackage	Qty.	Carrier	
DMP31D1U-7	SOT23	3,000	Tape & Reel	
DMP31D1U-13	SOT23	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead, Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BG7 = Product Type Marking Code YM = Date Code Marking \overline{Y} = Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	N	0	Р	R	S	Т	U	V
Month		F.1						_				
WOITH	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Cha	racteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			Vgss	±8	V
Continuous Drain Current	Steady State	$T_A = +25^{\circ}C \text{ (Note 5)}$ $T_A = +70^{\circ}C \text{ (Note 5)}$	ID	-0.62 -0.5	Α
Maximum Continuous Body Diode Forward Current (Note 5)			Is	-0.65	A
Pulsed Drain Current (10µs Pu	ulse, Duty Cy	/cle = 1%)	I _{DM}	-2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		PD	0.46	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	274	°C/W
Total Power Dissipation (Note 5)		PD	0.58	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	214	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

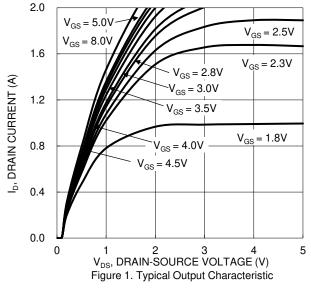
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

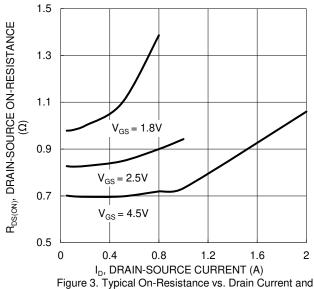
	1					
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	1	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	I	_	-1	μΑ	$V_{DS} = -30V$, $V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	_	-1.1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
			0.6	1		V _{GS} = -4.5V, I _D = -400mA
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.8	1.5	Ω	$V_{GS} = -2.5V, I_D = -200mA$
			0.9	2		$V_{GS} = -1.8V, I_{D} = -100mA$
Diode Forward Voltage	VsD	I	-0.8	-1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		54	_	pF	
Output Capacitance	Coss	I	10.9	_	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	5.8	_	pF	1 - 1.000112
Total Gate Charge	Q_g	1	1.0	_	nC	$V_{GS} = -4.5V, V_{DS} = -15V, I_{D} = -1A$
Total Gate Charge	Qg	1	1.6	_	nC	V 0V V 45V
Gate-Source Charge	Qgs	l	0.2	_	nC	VGS = -8V, VDS = -15V
Gate-Drain Charge	Q_{gd}	1	0.1	_	nC	ID = -1A
Turn-On Delay Time	t _{D(ON)}	_	3.8	_	ns	
Turn-On Rise Time	tr	_	11	_	ns	$V_{DD} = -10V$, $R_L = 10\Omega$
Turn-Off Delay Time	tD(OFF)	_	45	_	ns	$V_{GS} = -4.5V$, $R_{G} = 6\Omega$
Turn-Off Fall Time	t _F	_	20	_	ns	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







Gate Voltage

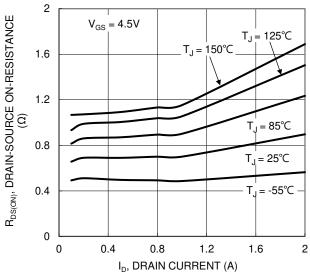
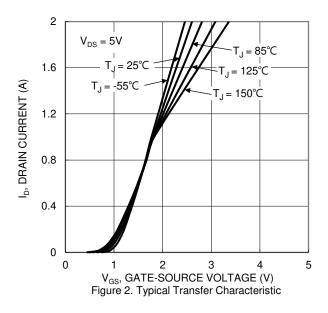
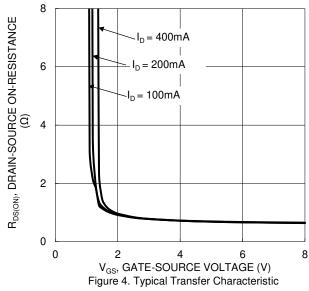


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





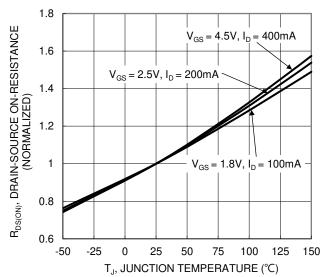


Figure 6. On-Resistance Variation with Junction Temperature



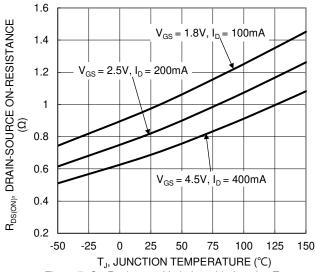
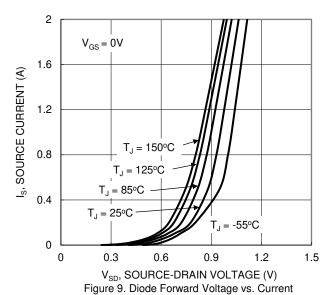
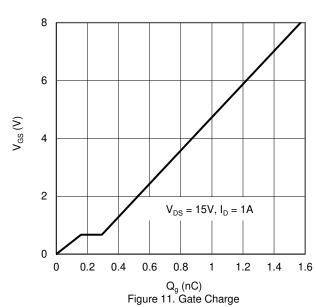


Figure 7. On-Resistance Variation with Junction Temperature





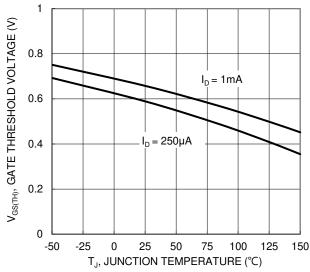
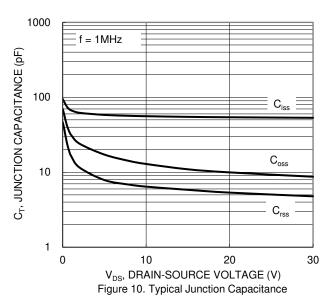


Figure 8. Gate Threshold Variation vs. Junction Temperature



10 R_{DS(ON)} 1 $P_W = 100 \mu s$ $P_W = 10ms$ ID, DRAIN CURRENT (A) P_W = 100ms 0.1 T_{J(Max)} = 150°C T_C = 25°C Single Pulse DUT on 1*MRP = 10sBoard $V_{GS} = 8V$ DC 0.01 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



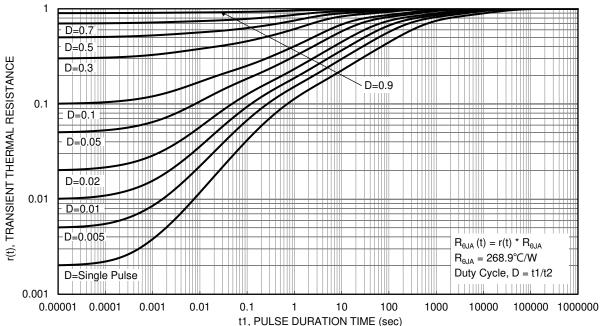


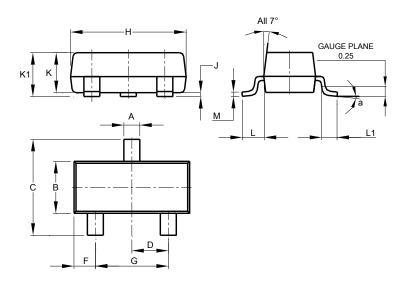
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT23

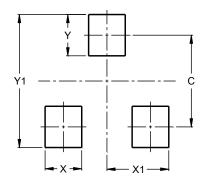


	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Η	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890 1.		0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°	_					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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